

# CD4041UB Types

## CMOS Quad True/Complement Buffer

### High Voltage Types (20-Volt Rating)

■ CD4041UB types are quad true/complement buffers consisting of n- and p-channel units having low channel resistance and high current (sourcing or sinking) capability. The CD4041UB is intended for use as a buffer, line driver, or CMOS-to-TTL driver. It can be used as an ultra-low power resistor-network driver for A/D and D/A conversion, as a transmission-line driver, and in other applications where high noise immunity and low power dissipation are primary design requirements.

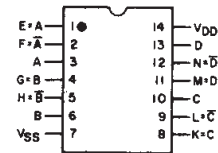
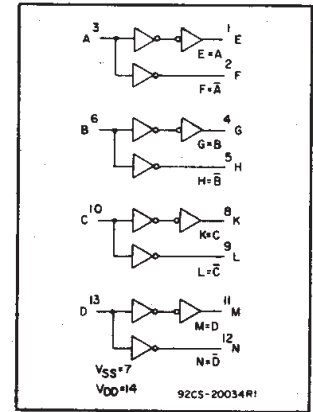
The CD4041UB types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

### Features:

- Balanced sink and source current; approximately 4 times standard "B" drive
- Equalized delay to true and complement outputs
- 100% tested for quiescent current at 20 V
- Maximum input current of 1  $\mu$ A at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

### Applications:

- High current source/sink driver
- CMOS-to-DTL/TTL Converter Buffer
- Display driver
- MOS clock driver
- Resistor network driver (Ladder or weighted R)
- Buffer
- Transmission line driver



92CS-20755R1

### TOP VIEW TERMINAL ASSIGNMENT

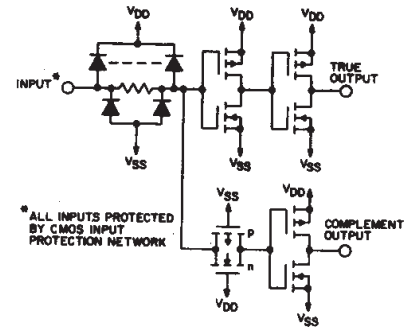


Fig. 1 - Schematic diagram 1 of 4 buffers.

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V <sub>DD</sub> ) Voltages referenced to V <sub>SS</sub> Terminal)	-0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to V <sub>DD</sub> +0.5V
DC INPUT CURRENT, ANY ONE INPUT	±10mA
POWER DISSIPATION PER PACKAGE (P <sub>D</sub> ):	
For T <sub>A</sub> = -55°C to +100°C	500mW
For T <sub>A</sub> = +100°C to +125°C	Derate Linearly at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR T <sub>A</sub> = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE (T <sub>A</sub> )	-55°C to +125°C
STORAGE TEMPERATURE RANGE (T <sub>stg</sub> )	-65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max	+265°C

### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following range:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T <sub>A</sub> =Full Package-Temperature Range)	3	18	V

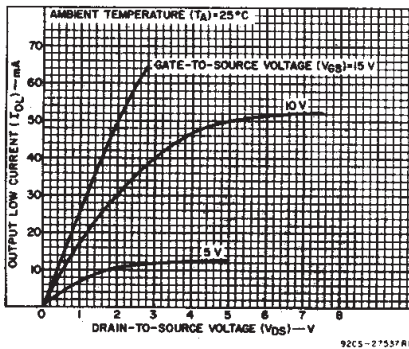


Fig. 2 - Typical output low (sink) current characteristics.

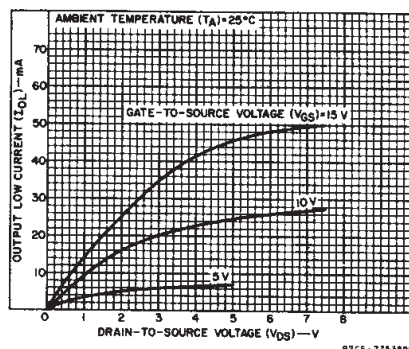


Fig. 3 - Minimum low (sink) current characteristics.

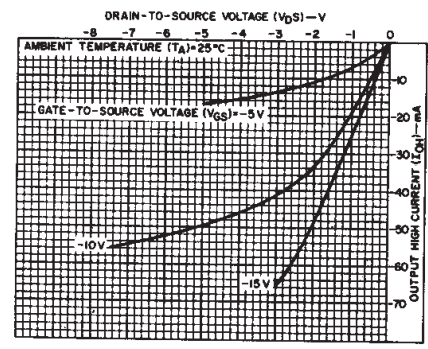


Fig. 4 - Typical output high (source) current characteristics.

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COMMERCIAL CMOS  
HIGH VOLTAGE ICs

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## STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current I <sub>DD</sub> Max.	—	0.5	5	1	1	30	30	—	0.02	1	μA
	—	0.10	10	2	2	60	60	—	0.02	2	
	—	0.15	15	4	4	120	120	—	0.02	4	
	—	0.20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current, I <sub>OL</sub> Min.	0.4	0.5	5	2.1	1.8	1.3	1.2	1.6	3.2	—	mA
	0.5	0.10	10	6.25	5.6	4	3.5	5	10	—	
	1.5	0.15	15	24	23	15.5	13	19	38	—	
	4.6	0.5	5	-2.1	-1.8	-1.3	-1.2	-1.6	-3.2	—	
Output High (Source) Current, I <sub>OH</sub> Min.	2.5	0.5	5	-8.4	-6.7	-5.3	-4.6	-6.4	-12.8	—	mA
	9.5	0.10	10	-6.25	-5.6	-4	-3.5	-5	-10	—	
	13.5	0.15	15	-24	-23	-15.5	-13	-19	-38	—	
	—	—	—	—	—	—	—	—	—	—	
Output Voltage: Low-Level, V <sub>OL</sub> Max.	—	0.5	5	0.05				—	0	0.05	V
	—	0.10	10	0.05				—	0	0.05	
	—	0.15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V <sub>OH</sub> Min.	—	0.5	5	4.95				4.95	5	—	V
	—	0.10	10	9.95				9.95	10	—	
	—	0.15	15	14.95				14.95	15	—	
Input Low Voltage, V <sub>IL</sub> Max.	0.5, 4.5	—	5	1				—	—	1	V
	1.9	—	10	2				—	—	2	
	1.5, 13.5	—	15	2.5				—	—	2.5	
Input High Voltage, V <sub>IH</sub> Min.	0.5, 4.5	—	5	4				4	—	—	V
	1.9	—	10	8				8	—	—	
	1.5, 13.5	—	15	12.5				12.5	—	—	
Input Current, I <sub>IN</sub> Max.	—	0.18	18	±0.1	±0.1	±1	±1	—	±10 <sup>-5</sup>	±0.1	μA

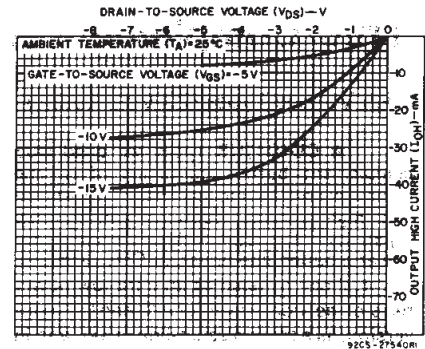


Fig. 5 - Minimum output high (source) current characteristics.

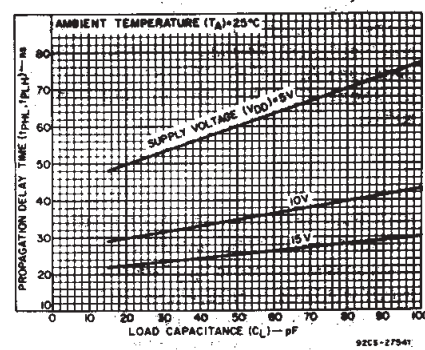


Fig. 6 - Typical propagation delay time vs. load capacitance.

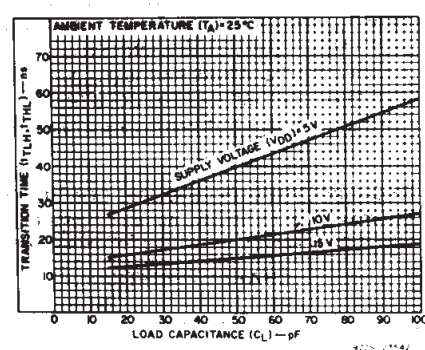


Fig. 7 - Typical transition time vs. load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS at T<sub>A</sub> = 25°C, Input t<sub>r</sub>, t<sub>f</sub> = 20 ns, C<sub>L</sub> = 50 pF, R<sub>L</sub> = 200 kΩ

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS
		V <sub>DD</sub> Volts	Typ. Max.	
Propagation Delay Time: t <sub>PHL</sub> t <sub>PLH</sub>	Any Input	5	60 120	ns
		10	35 70	
		15	25 50	
Transition Time t <sub>THL</sub> t <sub>TLH</sub>	Any Input	5	40 80	ns
		10	20 40	
		15	15 30	
Input Capacitance	C <sub>IN</sub>	Any Input	15 22.5	pF

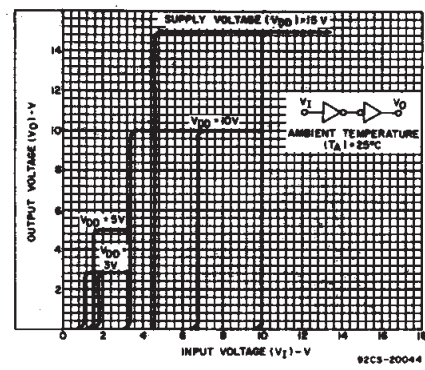


Fig. 8 - Minimum and maximum transfer characteristics - true output.

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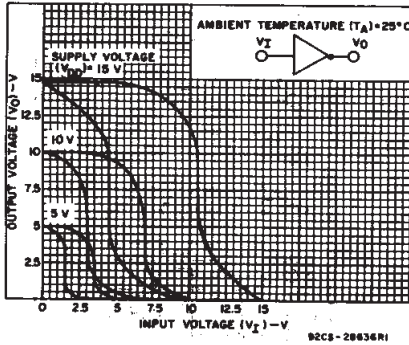


Fig. 9 - Minimum and maximum transfer characteristics - complement output.

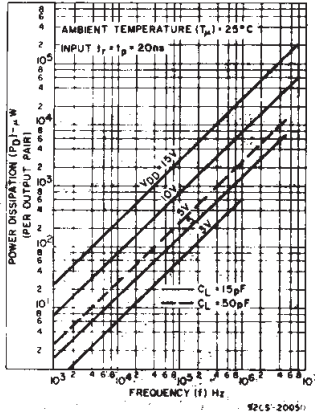


Fig. 11 - Typical power dissipation vs frequency per output pair.

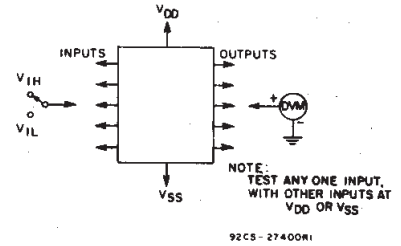


Fig. 13 - Input voltage test circuit.

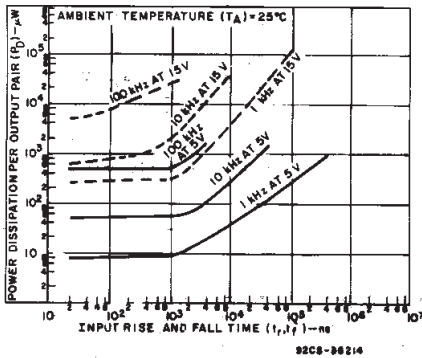


Fig. 10 - Typical power dissipation vs. input rise & fall time per output pair.

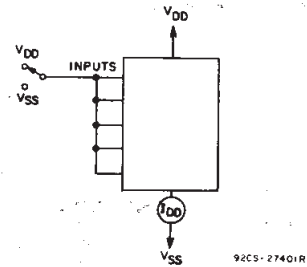


Fig. 12 - Quiescent device current test circuit.

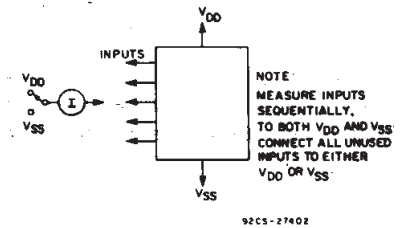
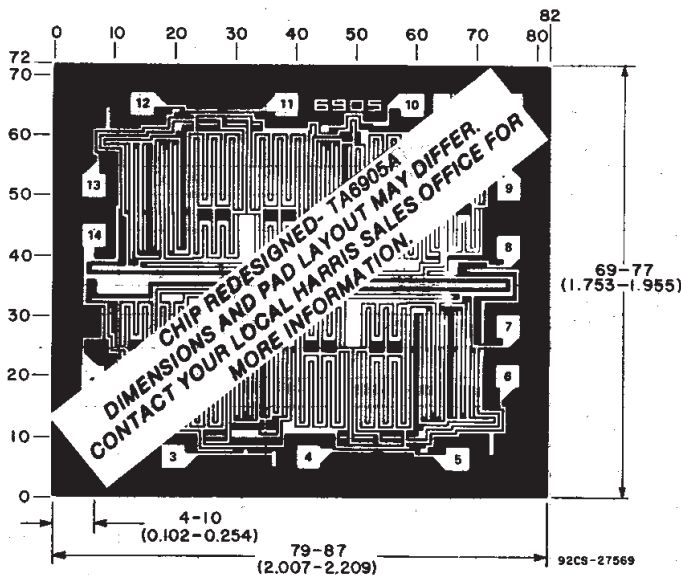


Fig. 14 - Input-leakage-current test circuit.

## Dimensions and pad layout for the CD4041UBH



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).

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